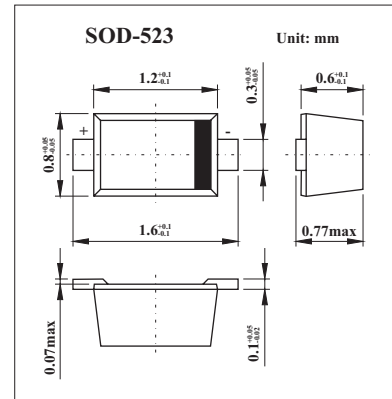


Silicon Epitaxial Planar Pin Diode

HVC133



■ Features

- Low capacitance. (C=1.0pF max)
- Low forward resistance. ($r_f=0.7\ \Omega$ max)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	30	V
Power dissipation	P_d	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse voltage	V_R	$I_R = 1\ \mu\text{A}$	30			V
Reverse current	I_R	$V_R = 25\ \text{V}$			100	nA
Forward voltage		$I_F = 2\ \text{mA}$			0.85	V
Capacitance	C1	$V_R = 1\ \text{V}, f = 1\ \text{MHz}$			1.0	pF
	C6	$V_R = 6\ \text{V}, f = 2\ \text{MHz}$			0.9	
Forward resistance	r_f	$I_F = 2\ \text{mA}, f = 100\ \text{MHz}$		0.55	0.7	Ω

■ Marking

Marking	P3
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